

Fast asymmetric thyristor modules 1

Type	V_{DRM} $V_{DSM} = V_{DRM}$	V_{RRM} ($V_{RRM(C)}$) $t_p = 1 \mu s$	I_{TRMSM}	I_{TSM} 10 ms, $t_{vj \max}$	$\int i^2 dt$ 10 ms, $t_{vj \max}$	I_{TAVM}/t_C 180°el sin. A/°C	$V_{(TO)}$ $t_{vj} =$ $t_{vj \max}$	r_T $t_{vj} =$ $t_{vj \max}$	$(di/dt)_{cr}$ DIN IEC 747-6 A/ μs	t_q 1)	$(dv/dt)_{cr}$ DIN IEC 747-6 V/ μs	R_{thJC} 180°el sin. °C/W	R_{thCK} °C/W	$t_{vj \max}$ °C	Outline
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Modules with compression bonding

AD 50 F	800 1000 1100 1200 1300*	15 (50)	120	1300	8450	76/56 50/85	1,3	3,75	120	E ≤ 20 D ≤ 15 C ≤ 12 B ≤ 10 A ≤ 8 ²⁾	C = 500 F = 1000	0,45	0,16	125	49
AD 60 F	800 1000 1100 1200 1300*	15 (50)	150	1450	10500	95/56 60/85	1,2	2,80	120	E ≤ 20 D ≤ 15 C ≤ 12 B ≤ 10 A ≤ 8 ²⁾	C = 500 F = 1000	0,39	0,16	125	49
AD 96 S	800 1000 1100 1200 1300*	15 (50)	200	2350	27600	127/67 95/85	1,3	2,15	400	D ≤ 15 C ≤ 12 B ≤ 10 A ≤ 8 ²⁾	C = 500 F = 1000	0,23	0,06	125	53
AD 116 S	800 1000 1100 1200 1300*	15 (50)	220	2600	33800	140/74 115/85	1,1	1,45	400	E ≤ 20 D ≤ 15	C = 500 F = 1000	0,23	0,06	125	53
AD 180 S	800 1000 1100 1200 1300*	15 (50)	350	4800	115000	223/73 180/85	1,3	0,9	500	D ≤ 15 C ≤ 12 B ≤ 10 A ≤ 8 ²⁾	C = 500 F = 1000	0,13	0,04	125	54
AD 220 S	800 1000 1100 1200 1300*	15 (50)	410	5200	135000	261/75 220/85	1,1	0,6	500	F ≤ 25 E ≤ 20 D ≤ 15	C = 500 F = 1000	0,13	0,04	125	54

1) With fast inverse diode

2) $V_{DRM} \leq 1000$ V